

L Number	Hits	Search Text	DB	Time stamp
-	6009	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:08
-	1	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and metallic and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:40
-	0	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) with metallic and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:16
-	1	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (metallic or(metal\$4 adj clusters)) and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:18
-	1	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:20
-	1	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:22
-	3	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:25
-	647766	(metallic or(metal\$4 adj (cluster\$1 or element\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/21 16:52
-	0	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first and third) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:48

-	0	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first and third) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2 adj element) and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:30
-	23348	((second and first and third) adj (semiconductor (film\$1 or layer\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:34
-	0	((metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first and third) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:37
-	3	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first) adj (film\$1 or layer\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:39
-	1	((((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and metallic and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)) and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:41
-	15096	getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:26
-	2810	((metallic or(metal\$4 adj (cluster\$1 or element\$1))) and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:43
-	12	((metallic or(metal\$4 adj (cluster\$1 or element\$1))) and getter\$3) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:44
-	0	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1))) and ((second and first and third) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:52
-	0	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1))) and ((first and second and third) adj (film\$1 or layer\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:54
-	5	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1))) and (first adj (film\$1 or layer\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:27
-	9	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1))) and (semiconductor adj (film\$1 or layer\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:56

-	8595	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:28
-	0	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:31
-	1086	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:32
-	715	((metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous) and crystall\$4	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:32
-	189	((metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous) and crystall\$4) and inert adj gas\$2	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:33
-	14	((metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous) and crystall\$4) and inert adj gas\$2) and (barrier adj (layer or film))	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:33
-	6	((("6087679") or ("6077731") or ("6147667") or ("6133073") or ("6168980") or ("6107639")).PN.	USPÄT; US-PGPUB	2002/06/07 13:54
-	4	((("6087679") or ("6077731") or ("6147667") or ("6133073") or ("6168980") or ("6107639")).PN.) and barrier	USPAT; US-PGPUB	2002/06/07 14:52
-	3	((("6087679") or ("6077731") or ("6147667") or ("6133073") or ("6168980") or ("6107639")).PN.) and barrier) and block\$3	USPAT; US-PGPUB	2002/06/07 14:51
-	1	((("6396147").PN.) and barrier	USPAT; US-PGPUB	2002/06/07 14:53
-	1	((("6396147").PN.) and barrier) and amorphous	USPAT; US-PGPUB	2002/06/07 14:53
-	1	((("6396147").PN.) and barrier) and amorphous) and crystal\$4	USPAT; US-PGPUB	2002/06/07 14:53
-	1	((("6396147").PN.) and barrier) and amorphous) and crystal\$4) and inert adj gas	USPAT; US-PGPUB	2002/06/07 14:54
-	1	((("6396147").PN.) and barrier) and amorphous) and crystal\$4) and inert adj gas) and getter\$3	USPAT; US-PGPUB	2002/06/07 14:54
-	835	((438/166) or (438/486) or (438/476)).CCLS.	USPAT; US-PGPUB	2002/06/08 13:58
-	215	((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3	USPAT; US-PGPUB	2002/06/08 14:43
-	28	((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and (inert or noble) adj gas	USPAT; US-PGPUB	2002/06/08 14:43
-	9	((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and (inert or noble) adj gas) and barrier	USPAT; US-PGPUB	2002/06/08 14:44
-	0	("FOR0146").PN.	USPAT; US-PGPUB	2002/06/08 14:08
-	0	("FOR0146").PN.	JPO; DERWENT; IBM_TDB	2002/06/10 19:02
-	96	((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and amorphous	USPÄT; US-PGPUB	2002/06/08 14:43

-	16	(((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and amorphous) and (inert or noble) adj gas	USPAT; US-PGPUB	2002/06/08 14:43
-	6	(((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and amorphous) and (inert or noble) adj gas) and barrier	USPAT; US-PGPUB	2002/06/08 14:44
-	1	("6396147").PN.	USPAT; US-PGPUB	2002/06/10 17:37
-	1	("5789284").PN.	USPAT; US-PGPUB	2002/06/10 17:37
-	0	("FOR 146").PN.	JPO; DERWENT; IBM_TDB	2002/06/10 19:04
-	9	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) with (anneal\$ with (electric adj current))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/21 16:53
-	1	("20020086469").PN.	USPAT; US-PGPUB	2003/06/02 17:02
-	19346	kim.in.	USPAT; US-PGPUB	2003/06/02 17:02
-	8679	getter\$3	USPAT; US-PGPUB	2003/06/02 17:03
-	44	kim.in. and getter\$3	USPAT; US-PGPUB	2003/06/02 17:03
-	16337	getter\$3 or getter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:50
-	2089	"semiconductor energy laboratory"	USPAT; US-PGPUB	2003/06/03 13:52
-	19706	tft or (thin adj film adj transistor)	USPAT; US-PGPUB	2003/06/03 13:58
-	641	(getter\$3 or getter) and (tft or (thin adj film adj transistor))	USPAT; US-PGPUB	2003/06/03 14:00
-	248	((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory"	USPAT; US-PGPUB	2003/06/03 14:00
-	40	((((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<20010216) and 438/\$.ccls.	USPAT; US-PGPUB	2003/06/03 14:02
-	111	((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<20010216	USPAT; US-PGPUB	2003/06/03 18:03
-	32627	ozone	USPAT; US-PGPUB	2003/06/03 18:02
-	110	((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<20010216	USPAT; US-PGPUB	2003/06/03 18:03
-	3	ozone and (((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<20010216)	USPAT; US-PGPUB	2003/06/03 18:12
-	66319	deioniz\$3	USPAT; US-PGPUB	2003/06/03 18:13
-	0	((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<20010216) and deioniz\$3	USPAT; US-PGPUB	2003/06/03 18:13
-	556	((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.	USPAT; US-PGPUB	2003/06/06 12:37
-	18319	amorphous\$3 and crystal\$8 and laser	USPAT; US-PGPUB	2003/06/06 12:38

-	692277	barrier or (oxide or nitride or oxynitride)	USPAT; US-PGPUB	2003/06/06 12:38
-	61	((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)	USPAT; US-PGPUB	2003/06/06 12:38
-	57	((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)) and (barrier or (oxide or nitride or oxynitride))	USPAT; US-PGPUB	2003/06/06 14:19
-	57	((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)) and (barrier or (oxide or nitride or oxynitride))	USPAT; US-PGPUB	2003/06/06 14:22
-	5183	catalytic near metal	USPAT; US-PGPUB	2003/06/06 14:24
-	1	((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)) and (barrier or (oxide or nitride or oxynitride))) and (catalytic near metal)	USPAT; US-PGPUB	2003/06/06 14:21
-	112610	amorphous\$3	USPAT; US-PGPUB	2003/06/06 14:22
-	505011	crystal\$8	USPAT; US-PGPUB	2003/06/06 14:23
-	260315	laser	USPAT; US-PGPUB	2003/06/06 14:23
-	692277	barrier or (oxide or nitride or oxynitride)	USPAT; US-PGPUB	2003/06/06 15:22
-	28707	(catalytic or cluster or element) near metal	USPAT; US-PGPUB	2003/06/06 14:25
-	2556	crystal\$8 same ((catalytic or cluster or element) near metal)	USPAT; US-PGPUB	2003/06/06 14:25
-	1285	(crystal\$8 same ((catalytic or cluster or element) near metal)) and amorphous\$3	USPAT; US-PGPUB	2003/06/06 14:25
-	709	((crystal\$8 same ((catalytic or cluster or element) near metal)) and amorphous\$3) and laser	USPAT; US-PGPUB	2003/06/06 14:26
-	676	((crystal\$8 same ((catalytic or cluster or element) near metal)) and amorphous\$3) and laser) and (barrier or (oxide or nitride or oxynitride))	USPAT; US-PGPUB	2003/06/06 14:26
-	8423	getter or gettering	USPAT; US-PGPUB	2003/06/06 14:26
-	233	((crystal\$8 same ((catalytic or cluster or element) near metal)) and amorphous\$3) and laser) and (barrier or (oxide or nitride or oxynitride)) and (getter or gettering)	USPAT; US-PGPUB	2003/06/06 14:45
-	5636607	(fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)	USPAT; US-PGPUB	2003/06/06 14:50
-	124463	((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8	USPAT; US-PGPUB	2003/06/06 14:51
-	29298	amorphous\$3 and ((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)	USPAT; US-PGPUB	2003/06/06 14:51

-	22525	(amorphous\$3 and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and (barrier or (oxide or nitride or oxynitride))	USPAT; US-PGPUB	2003/06/06 14:51
-	690	((amorphous\$3 and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and (barrier or (oxide or nitride or oxynitride))) and (getter or gettering)	USPAT; US-PGPUB	2003/06/06 14:52
-	531	((amorphous\$3 and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and (barrier or (oxide or nitride or oxynitride))) and (getter or gettering)) and laser	USPAT; US-PGPUB	2003/06/06 14:52
-	133656	(barrier or (oxide or nitride or oxynitride)) near (film or layer)	USPAT; US-PGPUB	2003/06/06 15:23
-	14785	((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)	USPAT; US-PGPUB	2003/06/06 15:23
-	6367	((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and amorphous\$3	USPAT; US-PGPUB	2003/06/06 15:24
-	614	((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and amorphous\$3) and (getter or gettering)	USPAT; US-PGPUB	2003/06/06 15:24
-	511	((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and amorphous\$3) and (getter or gettering)) and laser	USPAT; US-PGPUB	2003/06/06 15:24
-	44	5821138.URPN.	USPAT	2003/06/06 15:49
-	5	("4838654" "5376561" "5488012" "5529937" "5618739").PN.	USPAT	2003/06/06 15:54
-	13	("4024626" "4759610" "4771016" "4838654" "4885616" "4906587" "4968638" "4980308" "4984033" "5110748" "5206749" "5256562" "5455187").PN.	USPAT	2003/06/06 15:54

-	13	("4024626" "4759610" "4771016" "4838654" "4885616" "4906587" "4968638" "4980308" "4984033" "5110748" "5206749" "5256562" "5455187").PN.	USPAT	2003/06/06 15:54
-	0	6337259.URPN.	USPAT	2003/06/06 16:14
-	1	"6140166".PN.	USPAT	2003/06/06 16:14
-	0	6337259.URPN.	USPAT	2003/06/06 16:15
-	0	6376336.URPN.	USPAT	2003/06/06 17:06
-	30	("3936858" "4498227" "5194395" "5244819" "5272104" "5443661" "5453153" "5501993" "5646053" "5753560" "5773152" "5795809" "5807771" "5818085" "5882990" "5899732" "5926727" "5929508" "5965917" "5976956" "6001711" "6010950" "6013584" "6022793" "6024888" "6083324" "6093624" "6100202" "6114223" "6133123").PN.	USPAT	2003/06/06 17:06
-	1	("5605847").PN.	USPAT; US-PGPUB	2003/06/15 11:57
-	1	("6097037").PN.	USPAT; US-PGPUB	2003/06/15 11:57
-	1	("6337259").PN.	USPAT; US-PGPUB	2003/06/15 12:10
-	36	funai.in.	USPAT; US-PGPUB	2003/06/15 16:13
-	1	("5550070").PN.	USPAT; US-PGPUB	2003/06/15 16:49